

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

) Art Unit: Unassigned

Hideomi SUZAWA et al.

) Examiner: Unassigned

Serial No. 10/086,628

)

Filed: March 4, 2002

)

For: SEMICONDUCTOR DEVICE AND)

MANUFACTURING METHOD

)

THEREOF

)

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with
The United States Postal Service with sufficient postage as First
Class Mail in an envelope addressed to: Commissioner for Patents,
Washington, D.C. 20231, on 27/3/02

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

Please preliminarily amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 7 and 11-12 as follows:

7. (Amended) A semiconductor device according to claims 1 to 5 wherein a side face of one of the source region and the drain is aligned with one of the source wiring and the electrode.

11. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 or 9 wherein in the eighth step, a part of the first amorphous semiconductor film and the conductive film and the second amorphous semiconductor film are etched with a chlorine type gas.

12. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 or 9 wherein the chlorine type gas is selected from Cl₂ and BCl₃, HCl and SiCl₄ or a gas containing a plurality of gases from these gases.

REMARKS

Applicants have amended claims 7 and 11-12 to correct the dependency.
Examination on the merits is respectfully requested.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 7 and 11-12 as follows:

7. (Amended) A semiconductor device according to claims 1 to [6] 5 wherein a side face of one of the source region and the drain is aligned with one of the source wiring and the electrode.

11. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 [to 10] or 9 wherein in the eighth step, a part of the first amorphous semiconductor film and the conductive film and the second amorphous semiconductor film are etched with a chlorine type gas.

12. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 [to 11] or 9 wherein the chlorine type gas is selected from Cl_2 and BCl_3 , HCl and SiCl_4 or a gas containing a plurality of gases from these gases.

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